TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM6N17FU

High Speed Switching Applications

Analog Switch Applications

- Suitable for high-density mounting due to compact package
- High drain-source voltage
- High speed switching

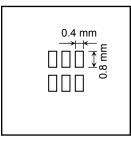
Absolute Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		V _{DS}	50	V	
Gate-Source voltage		V _{GSS}	±7	V	
Drain current	DC	I _D	100	mA	
	Pulse	I _{DP}	200		
Drain power dissipation (Ta = 25°C)		P _D (Note 1)	200	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

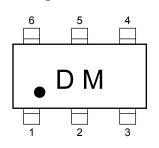
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

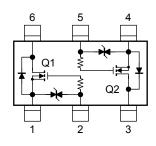
Note 1: Total rating,Mounted on FR4 board (25.4 mm × 25.4 mm × 1.6 t, Cu Pad: 0.32 mm² × 6)



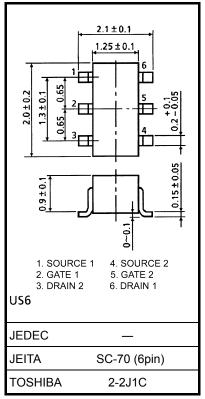
Marking



Equivalent Circuit



This transistor is a electrostatic sensitive device. Please handle with caution.



Weight: 6.8 mg (typ.)

Unit: mm

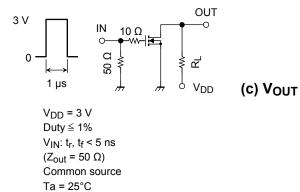
Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

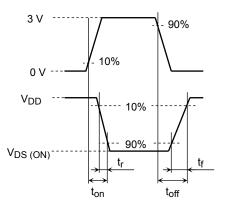
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 7 V, V_{DS} = 0$	_	_	±5	μA
Drain-Source breakdown voltage		V (BR) DSS	I _D = 0.1 mA, V _{GS} = 0	50	_	_	V
Drain cut-off curre	ent	I _{DSS}	V _{DS} = 50 V, V _{GS} = 0	_	_	1	μA
Gate threshold vo	ltage	V _{th}	V _{DS} = 3 V, I _D = 1 μA	0.9	_	1.5	V
Forward transfer	admittance	Y _{fs}	V _{DS} = 3 V, I _D = 10 mA	20	40	_	mS
Drain-Source ON resistance		R _{DS (ON)}	I _D = 10 mA, V _{GS} = 4 V	_	12	20	Ω
			I _D = 10 mA, V _{GS} = 2.5 V	_	22	40	
Input capacitance		C _{iss}	V _{DS} = 3 V, V _{GS} = 0, f = 1 MHz	_	7	_	pF
Reverse transfer capacitance		C _{rss}		_	3	_	pF
Output capacitance		C _{oss}]	_	7	_	pF
Switching time	Turn-on time	t _{on}	V _{DD} = 3 V, I _D = 20 mA, V _{GS} = 0~3 V, R _G = 10 Ω, R _L = 150 Ω	-	100	_	ns
	Turn-off time	t _{off}		—	40	—	

Switching Time Test Circuit

(a) Test circuit

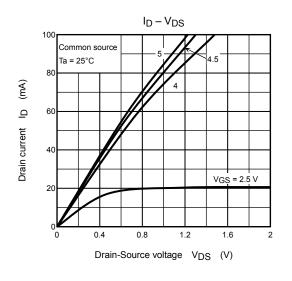
(b) V_{IN}

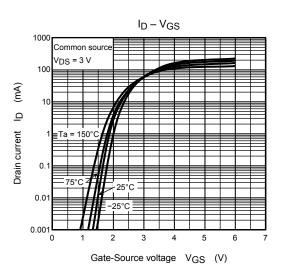


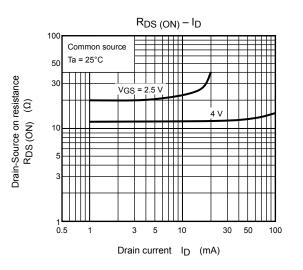


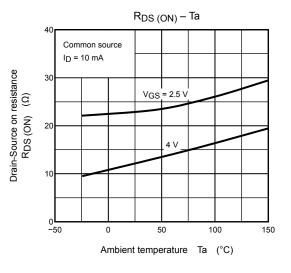
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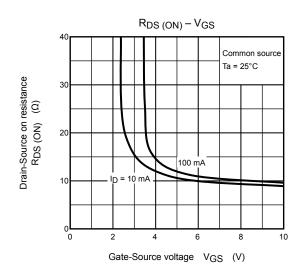
(Q1, Q2 Common)

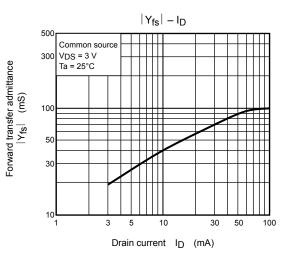






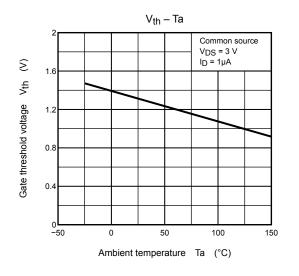


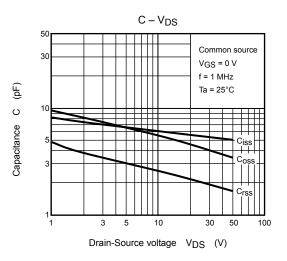


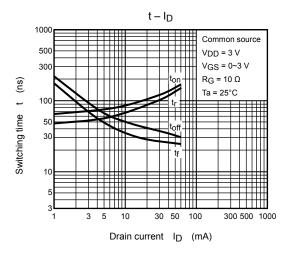


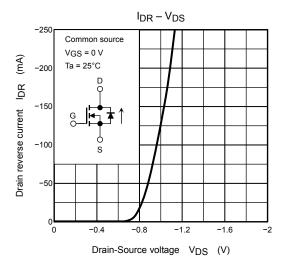
TOSHIBA

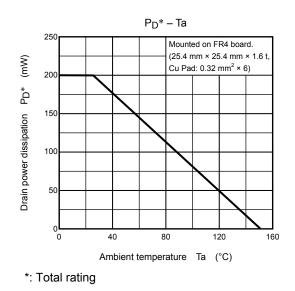
(Q1, Q2 Common)











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20070701-EN GENERAL

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